

N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY

| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) ^a | Q_g (Typ.) |
|--------------|----------------------------|------------------------|--------------|
| 30 | 0.0030 at $V_{GS} = 10$ V | 38 | 27.5 nC |
| | 0.0038 at $V_{GS} = 4.5$ V | 33 | |

FEATURES

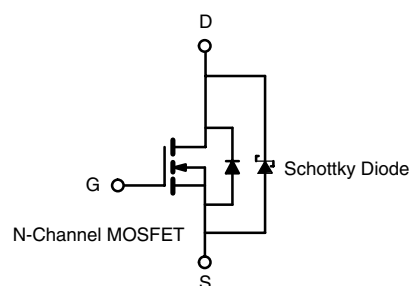
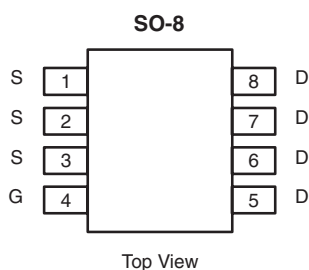
- Halogen-free According to IEC 61249-2-21 Definition
- SkyFET[®] Monolithic TrenchFET[®] Gen III Power MOSFET and Schottky Diode
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Notebook CPU Core
- Buck Converter



Ordering Information: Si4628DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

| Parameter | Symbol | Limit | Unit |
|--|----------------|---------------|----------------------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Continuous Drain Current ($T_J = 150$ °C) | I_D | $T_C = 25$ °C | 38 |
| | | $T_C = 70$ °C | 30 |
| | | $T_A = 25$ °C | 25.4 ^{b, c} |
| | | $T_A = 70$ °C | 20 ^{b, c} |
| Pulsed Drain Current | I_{DM} | 70 | A |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25$ °C | 7 |
| | | $T_A = 25$ °C | 3.1 ^{b, c} |
| Single Pulse Avalanche Current | I_{AS} | 45 | |
| Single Pulse Avalanche Energy | E_{AS} | 101 | mJ |
| Maximum Power Dissipation | P_D | $T_C = 25$ °C | 7.8 |
| | | $T_C = 70$ °C | 5 |
| | | $T_A = 25$ °C | 3.5 ^{b, c} |
| | | $T_A = 70$ °C | 2.2 ^{b, c} |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | °C |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Typ. | Max. | Unit |
|---|------------|------|------|------|
| Maximum Junction-to-Ambient ^{b, d} | R_{thJA} | 29 | 35 | °C/W |
| Maximum Junction-to-Foot (Drain) | R_{thJF} | 13 | 16 | |

Notes:

a. Based on $T_C = 25$ °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. $t = 10$ s.

d. Maximum under Steady State conditions is 80 °C/W.

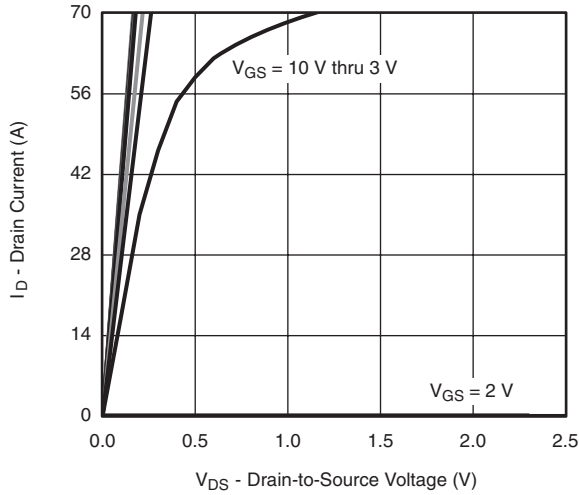
| SPECIFICATIONS T _J = 25 °C, unless otherwise noted | | | | | | |
|---|---------------------|---|------|--------|--------|------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 1 mA | 30 | | | V |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 1 mA | 1.0 | | 2.5 | |
| Gate-Source Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 20 V | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 30 V, V _{GS} = 0 V | | 0.10 | 0.25 | mA |
| | | V _{DS} = 30 V, V _{GS} = 0 V, T _J = 100 °C | | 7.5 | 70 | |
| On -State Drain Current ^a | I _{D(on)} | V _{DS} ≥ 5 V, V _{GS} = 10 V | 40 | | | A |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 10 V, I _D = 20 A | | 0.0024 | 0.0030 | Ω |
| | | V _{GS} = 4.5 V, I _D = 15 A | | 0.0030 | 0.0038 | |
| Forward Transconductance ^a | g _{fs} | V _{DS} = 15 V, I _D = 20 A | | 73 | | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz | | 3450 | | pF |
| Output Capacitance | C _{oss} | | | 810 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 260 | | |
| Total Gate Charge | Q _g | V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A | | 58 | 87 | nC |
| | | V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 20 A | | 27.5 | 42 | |
| Q _{gs} | | | 8.3 | | | |
| Q _{gd} | | | 7.5 | | | |
| Gate Resistance | R _g | f = 1 MHz | 0.4 | 1.7 | 3.4 | Ω |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω | | 28 | 55 | ns |
| Rise Time | t _r | | | 20 | 40 | |
| Turn-Off Delay Time | t _{d(off)} | | | 39 | 75 | |
| Fall Time | t _f | | | 13 | 26 | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω | | 12 | 24 | |
| Rise Time | t _r | | | 10 | 20 | |
| Turn-Off Delay Time | t _{d(off)} | | | 36 | 70 | |
| Fall Time | t _f | | | 9 | 18 | |
| Drain-Source Body Diode and Schottky Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | | | 7 | A |
| Pulse Diode Forward Current ^a | I _{SM} | | | | 70 | |
| Body Diode Voltage | V _{SD} | I _S = 2 A | | 0.44 | 0.53 | V |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = 13 A, dI/dt = 100 A/μs, T _J = 25 °C | | 28 | 55 | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | | | 21 | 42 | nC |
| Reverse Recovery Fall Time | t _a | | | 15 | | ns |
| Reverse Recovery Rise Time | t _b | | | 13 | | |

Notes:

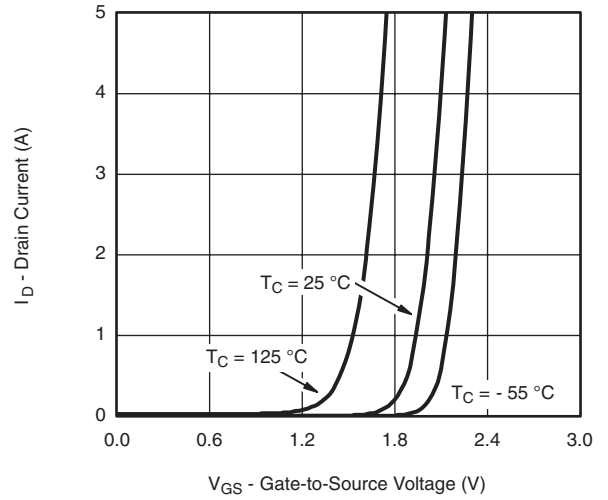
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

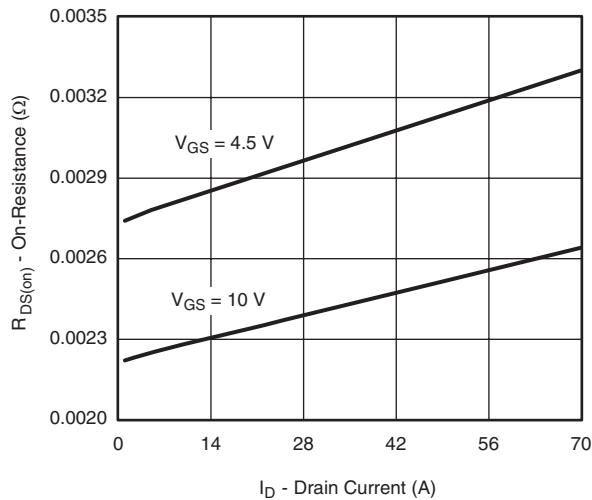
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



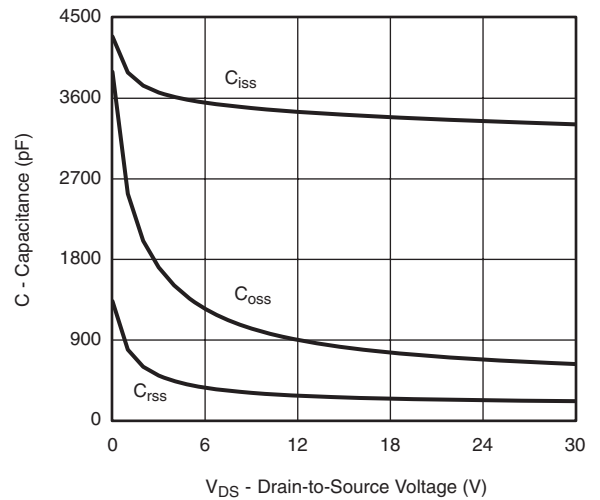
Output Characteristics



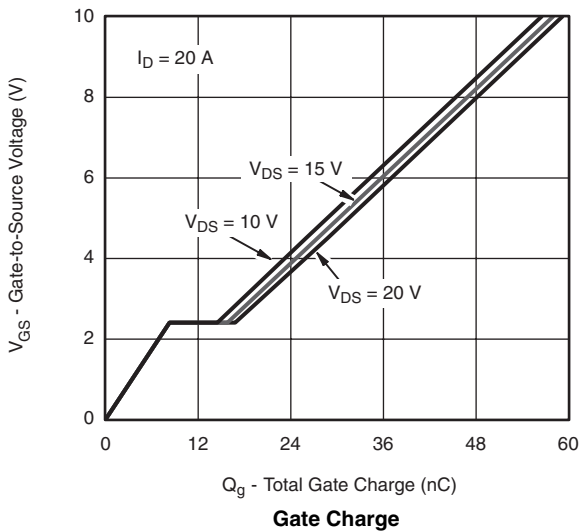
Transfer Characteristics



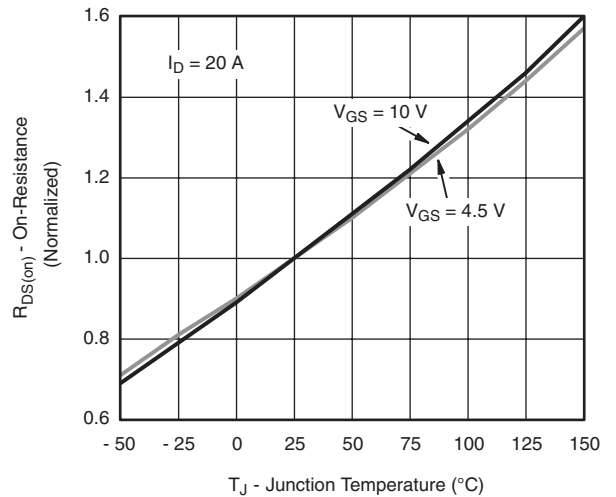
On-Resistance vs. Drain Current



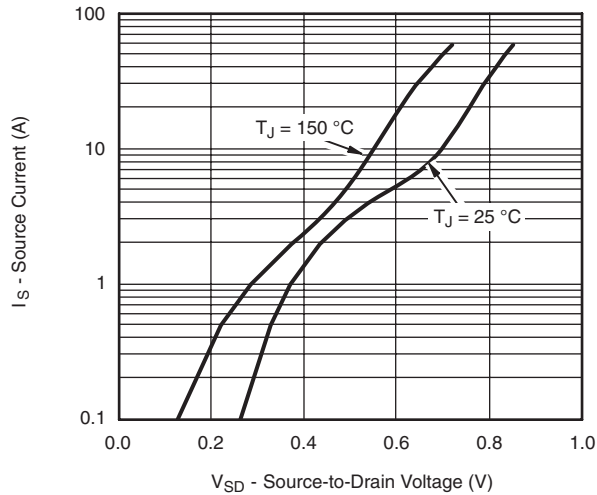
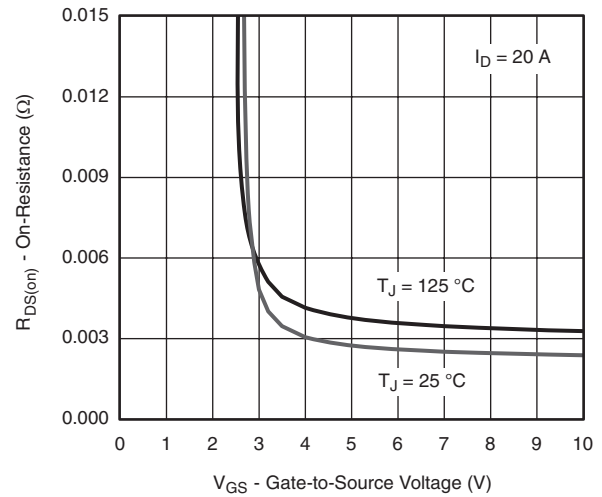
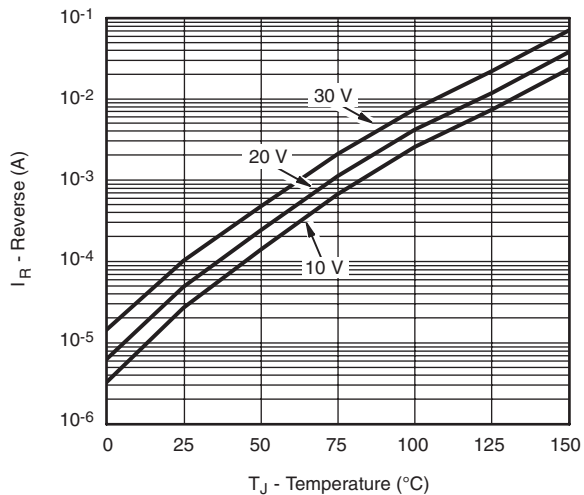
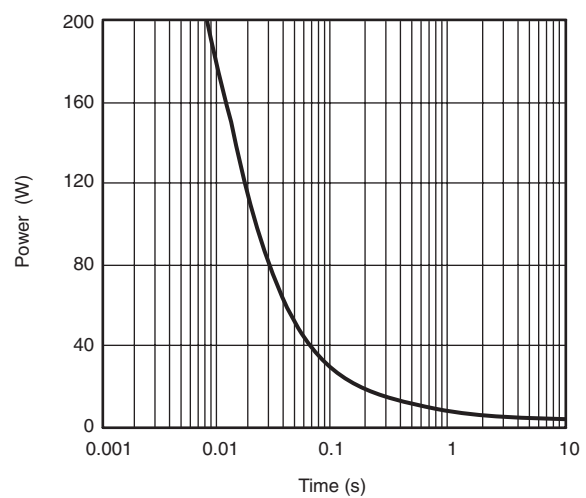
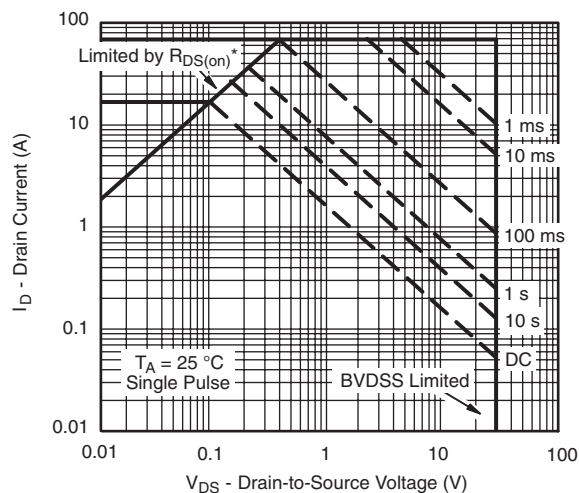
Capacitance



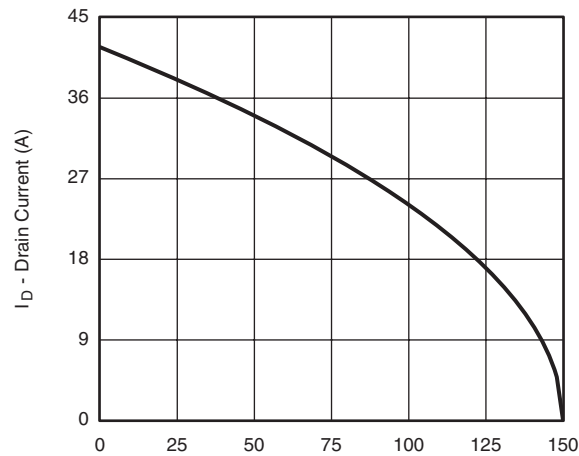
Gate Charge



On-Resistance vs. Junction Temperature

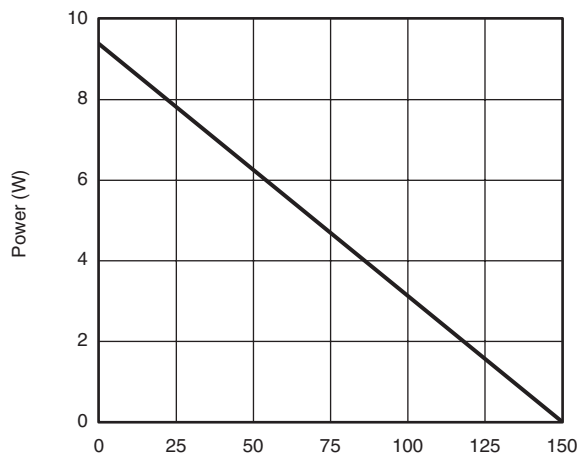
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Reverse Current (Schottky)****Single Pulse Power, Junction-to-Ambient*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area**

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



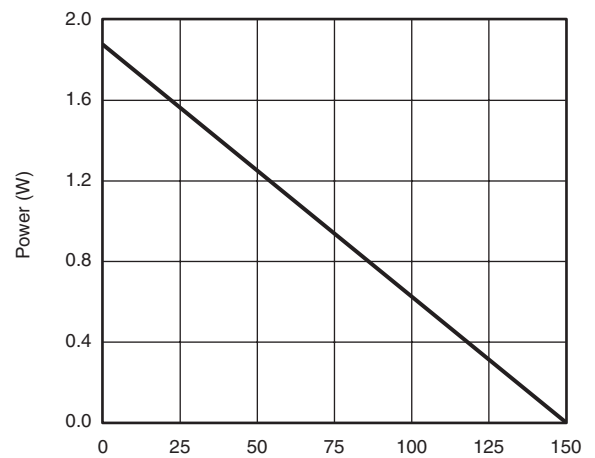
T_C - Case Temperature (°C)

Current Derating*



T_C - Case Temperature (°C)

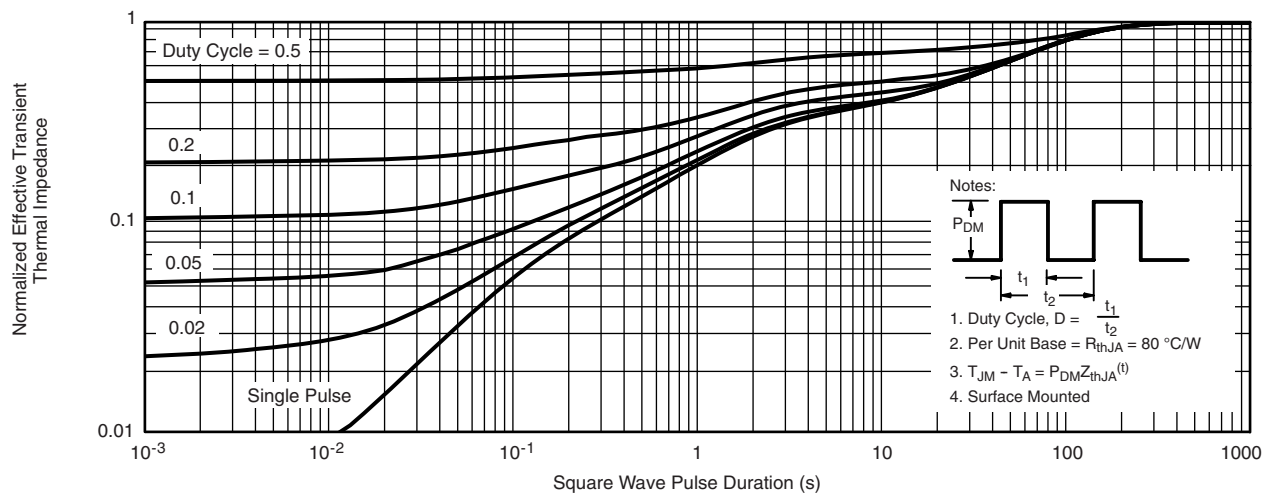
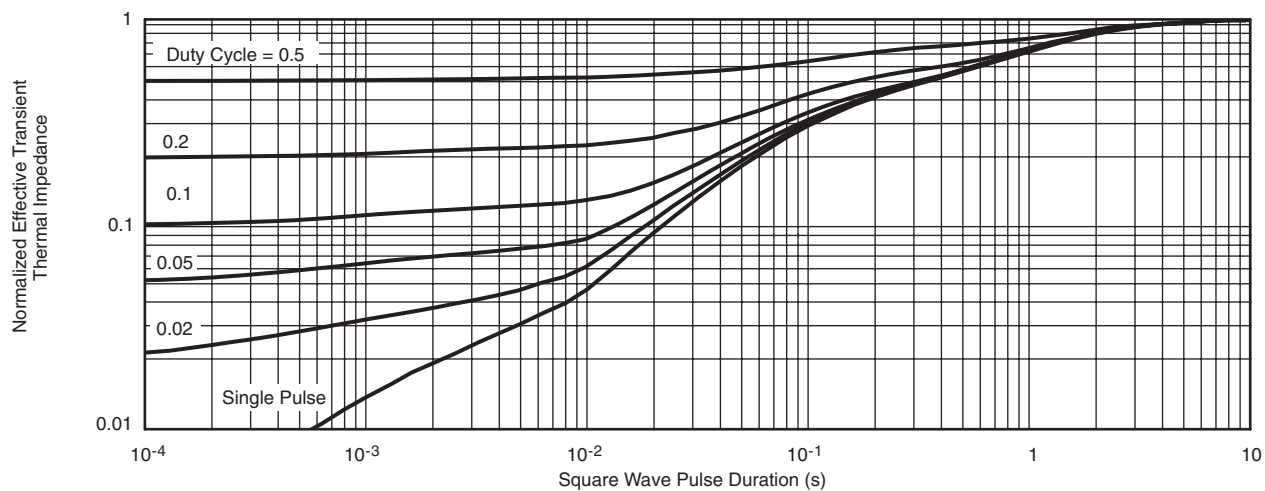
Power Derating, Junction-to-Foot



T_A - Ambient Temperature (°C)

Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



| DIM | MILLIMETERS | | INCHES | |
|--------------------------------|-------------|------|-----------|-------|
| | Min | Max | Min | Max |
| A | 1.35 | 1.75 | 0.053 | 0.069 |
| A ₁ | 0.10 | 0.20 | 0.004 | 0.008 |
| B | 0.35 | 0.51 | 0.014 | 0.020 |
| C | 0.19 | 0.25 | 0.0075 | 0.010 |
| D | 4.80 | 5.00 | 0.189 | 0.196 |
| E | 3.80 | 4.00 | 0.150 | 0.157 |
| e | 1.27 BSC | | 0.050 BSC | |
| H | 5.80 | 6.20 | 0.228 | 0.244 |
| h | 0.25 | 0.50 | 0.010 | 0.020 |
| L | 0.50 | 0.93 | 0.020 | 0.037 |
| q | 0° | 8° | 0° | 8° |
| S | 0.44 | 0.64 | 0.018 | 0.026 |
| ECN: C-06527-Rev. I, 11-Sep-06 | | | | |
| DWG: 5498 | | | | |

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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